C4MS008065L

Switching Optimized 650V 8mΩ Industrial Silicon Carbide Power MOSFET

Features

- Industry compatible drive voltage 15V...18V/-5V...0V
- Soft body diode with low Vds overshoot and ringing
- Low Rds(on) at high operating temperatures
- Improved device capacitance ratio (Ciss/Crss)
- High transient voltage robustness with improved lifetime
- Halogen free, RoHS compliant

Benefits

- Higher efficiency, lower switching losses and reduced EMI
- Faster switching operation enabling high power density
- Enables system level price performance optimization
- Reduction in system-level cooling requirements

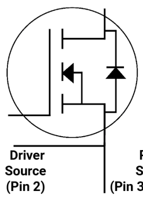
Typical Applications

- Data Center Power Supplies
- EV Chargers
- Solar/ESS
- Motor Control
- Industrial Power Supplies
- High Voltage DC/DC Converters

Package

Halogen-Free

RoHS compliant



Orderable Part Number	Package Type	Marking
C4MS008065L-TR	TOLL	C4MS008065L

Key Parameters

Parameter	Symbol	Min.	Typ.	Max	Unit	Conditions	Note
Drain–Source Voltage	V_{DS}			650	V		
Transient Drain–Source Voltage				750		<100 h throughout lifetime	Note 1
Maximum Gate–Source Voltage	$V_{GS(max)}$	-10		+23			Note 2
DC Continuous Drain Current	I_D		261		A	V_{GS} = 18 V, T_C = 25 °C, T_J ≤175 °C	Note 3
			187			V_{GS} = 18 V, T_C = 100 °C, T_J ≤175 °C	
Pulsed Drain Current	I_{DM}			619		t_{Pmax} limited by T_{Jmax} V_{GS} = 18 V, T_C = 25 °C	
Power Dissipation	P_D		825		W	T_C = 25 ˚C, T_J = 175 °C	Note 4
Operating Junction and Storage Temperature	T_J, T_{stg}	-55		+175	°C		
Solder Temperature	T_L			260		According to JEDEC J-STD-020	

Note (1): 100 hours of total accumulated lifetime of the product.
Note (2): When applying IPC-9592B or OCP M-CRPS derating standards, a maximum Gate-Source voltage (V_{GS}) of +25V is permissible.
Note (3): Current limit calculated by $I_{D(max)}=\sqrt{(P_D/R_{DS(typ)}(T_{J(max)},I_{D(max)}))}$
Note (4): $P_D=(T_J-T_C)/R_{th(JC,typ)}$

4600 Silicon Drive | Durham, NC 27703 | Tel: +1.919.313.5300 | wolfspeed.com/power

Electrical Characteristics (T_C = 25 ˚C unless otherwise specified)

Symbol	Parameter	Min.	Typ.	Max.	Unit	Test Conditions	Note
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	650			V	V_{GS} = 0 V, I_D = 100 µA	
$V_{GS(th)}$	Gate Threshold Voltage	2.0	2.6	3.9	V	V_{DS} = V_{GS}, I_D = 24.3 mA	Fig. 11
			2.0		V	V_{DS} = V_{GS}, I_D = 24.3 mA, T_J = 175 °C	
I_{DSS}	Zero Gate Voltage Drain Current		1	50	µA	V_{DS} = 650 V, V_{GS} = 0 V	
I_{GSS}	Gate–Source Leakage Current		10	250	nA	V_{GS} = 18 V, V_{DS} = 0 V	
$V_{GS(op)}$	Recommended Turn on Gate–Source Voltage		15…18		V		Refer to PRD-09634
	Recommended Turn off Gate–Source Voltage		-5…0				
$R_{DS(on)}$	Drain-Source On–State Resistance		8	10.4	mΩ	V_{GS} = 18 V, I_D = 88.4 A	Fig. 4, 5, 6
			11.8			V_{GS} = 18 V, I_D = 88.4 A, T_J = 175 °C	
			9.6			V_{GS} = 15 V, I_D = 88.4 A	
g_{fs}	Transconductance		51.3		S	V_{DS} = 20 V, I_D = 88.4 A	Fig. 7
			50.1			V_{DS} = 20 V, I_D = 88.4 A, T_J = 175 °C	
$R_{DS(on)Tempco}$	On resistance temperature coefficient		1.47			V_{GS} = 18 V, I_D = 88.4 A	Note 5
C_{iss}	Input Capacitance		6880		pF	V_{GS} = 0 V, V_{DS} = 400 V f = 100 kHz V_{AC} = 25 mV	Fig. 17, 18
C_{oss}	Output Capacitance		428				
C_{rss}	Reverse Transfer Capacitance		16				
C_{iss}/C_{rss}	Capacitance Ratio		430				Note 6
E_{oss}	C_{oss} Stored Energy		46		µJ		Fig. 16
$C_{o(er)}$	Effective Output Capacitance (Energy Related)		570		pF	V_{GS} = 0 V, V_{DS} = 0...400 V	Note 7
$C_{o(tr)}$	Effective Output Capacitance (Time Related)		936				
E_{on}	Turn-On Switching Energy (Body Diode FWD) T_J = 25 °C T_J = 175 °C		265 301		µJ	V_{DS} = 400 V, V_{GS} = -4 V/18 V I_D = 88.4 A, $R_{G(ext)}$ = 2 Ω, $L_σ$ = 25 nH	Fig. 25, 27, 29
E_{off}	Turn-Off Switching Energy (Body Diode FWD) T_J = 25 °C T_J = 175 °C		179 185				Fig. 25, 28, 29
$t_{d(on)}$	Turn-On Delay Time		19.3		ns	V_{DD} = 400 V, V_{GS} = -4 V/18 V I_D = 88.4 A, $R_{G(ext)}$ = 2 Ω, $L_σ$ = 25 nH Inductive load	Fig. 26, 27, 28, 29
t_r	Rise Time		8.2				
$t_{d(off)}$	Turn-Off Delay Time		61.7				
t_f	Fall Time		12.7				
$R_{G(int)}$	Internal Gate Resistance		1.32		Ω	f = 1 MHz	
Q_{gs}	Gate to Source Charge		77		nC	V_{DS} = 400 V, V_{GS} = -4 V/18 V I_D = 88.4 A Per IEC60747-8-4	Fig. 12
Q_{gd}	Gate to Drain Charge		64				
Q_g	Total Gate Charge		277				

Note (5): $R_{DS(on)Tempco}$ refers to $R_{DS(on)}$ at 175 C/ $R_{DS(on)}$ at 25C, C4MS 650V product family value
Note (6): Capacitance ratio is a FOM for Partial turn-on immunity PRD-06933, C4MS 650V product family value
Note (7): $C_{o(er)}$, a lumped capacitance that gives the same stored energy as C_{oss} while Vds is rising from 0 to 400 V
$C_{o(tr)}$, a lumped capacitance that gives the same charging time as C_{oss} while Vds is rising from 0 to 400 V

Reverse Diode Characteristics ($T_C = 25\,^{\circ}C$ unless otherwise specified)

Symbol	Parameter	Typ.	Max.	Unit	Test Conditions	Note
V_{SD}	Diode Forward Voltage	5.1		V	$V_{GS} = -4$ V, $I_{SD} = 44.2$ A	Fig. 8, 9, 10
		4.5		V	$V_{GS} = -4$ V, $I_{SD} = 44.2$ A, $T_J = 175$ °C	
I_S	Continuous Diode Forward Current	132		A	$V_{GS} = -4$ V	
I_{SM}	Diode Pulse Current		619	A	$V_{GS} = -4$ V, pulse width t_p limited by T_{Jmax}	
t_{rr}	Reverse Recovery Time	13.4		ns	$V_{SD} = 400$ V, $V_{GS} = -4$ V, $T_J = 175$ °C $I_S = 88.4$ A, $di_F/dt = 14.6$ A/ns	Fig. 30
Q_{rr}	Reverse Recovery Charge	839		nC		
I_{RRM}	Peak Reverse Recovery Current	103		A		
E_{RR}	Reverse recovery Energy $T_J = 25$ °C $T_J = 175$ °C	 259 302		µJ	$V_{DS} = 400$ V, $V_{GS} = -4$ V/18 V $I_D = 88.4$ A, $R_{G(on)} = 2\ \Omega$, $L_\sigma = 25$ nH	

Thermal Characteristics

Symbol	Parameter	Typ.	Max.	Unit	Test Conditions	Note
$R_{\theta JC}$	Thermal Resistance from Junction to Case	0.18		°C/W		

Typical Performance

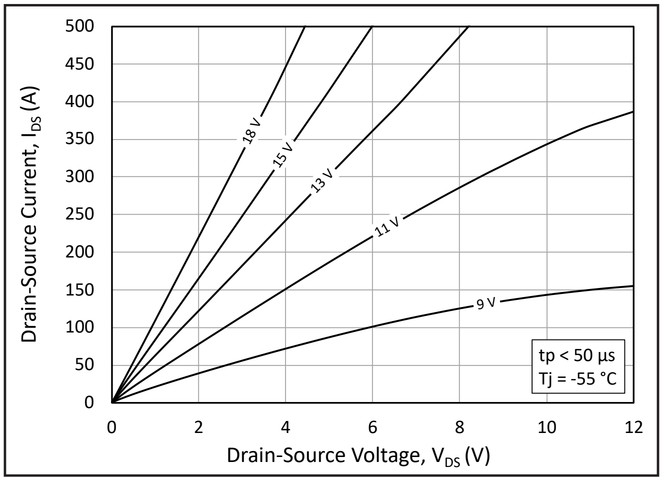


Figure 1. Output Characteristics T_J = -55°C

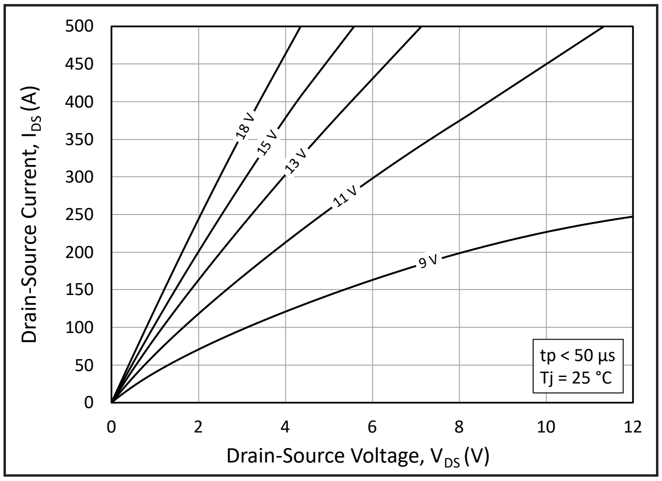


Figure 2. Output Characteristics T_J = 25°C

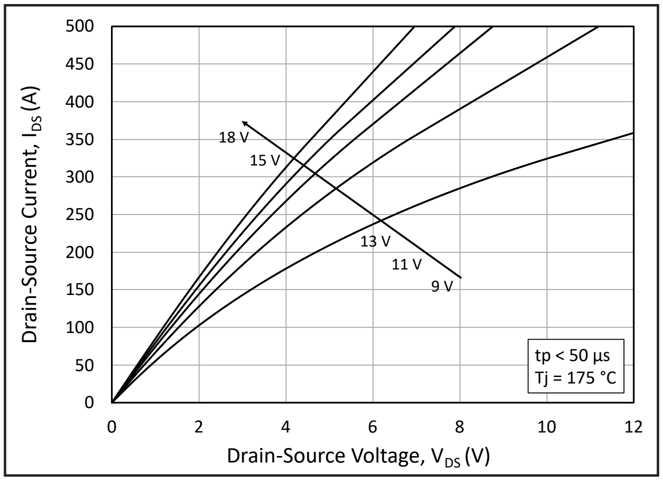


Figure 3. Output Characteristics T_J = 175°C

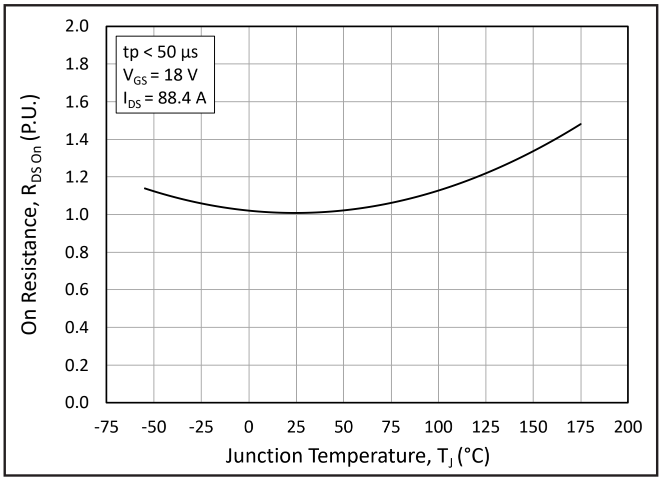


Figure 4. Normalized On-Resistance vs. Temperature

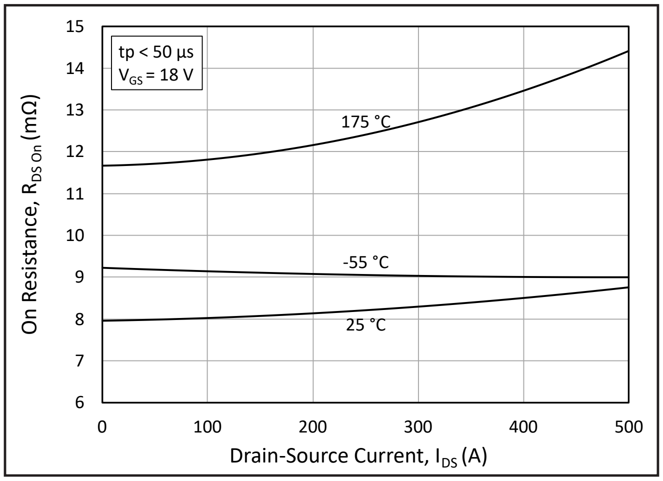


Figure 5. On-Resistance vs. Drain Current For Various Temperatures

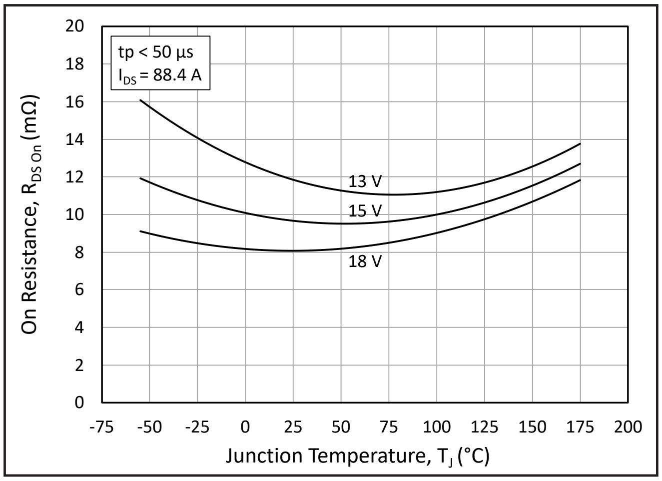


Figure 6. On-Resistance vs. Temperature For Various Gate Voltage

Typical Performance

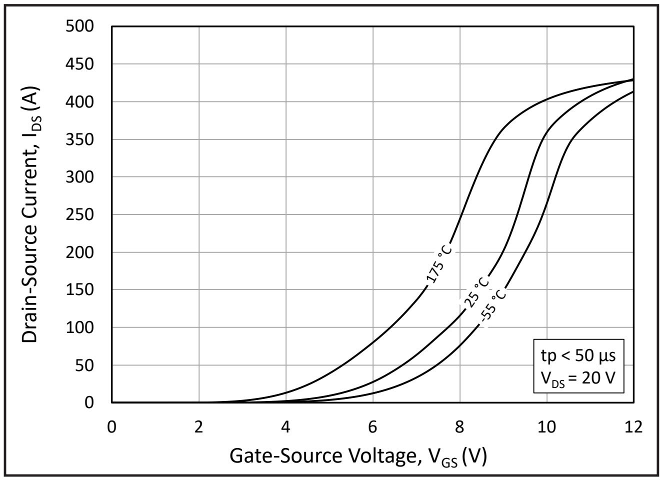


Figure 7. Transfer Characteristic for Various Junction Temperatures

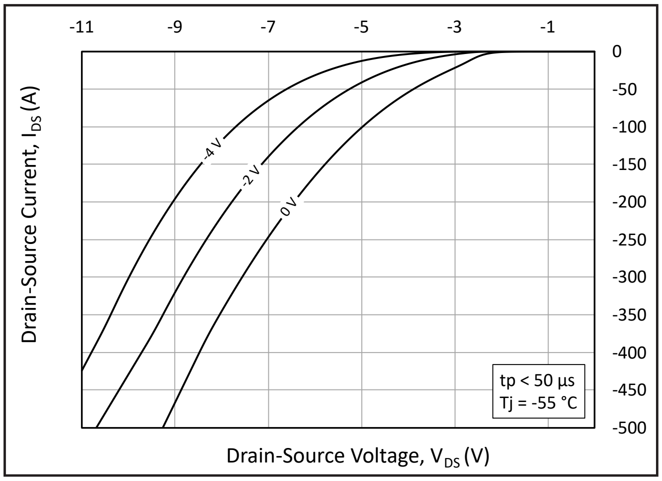


Figure 8. Body Diode Characteristic at -55°C

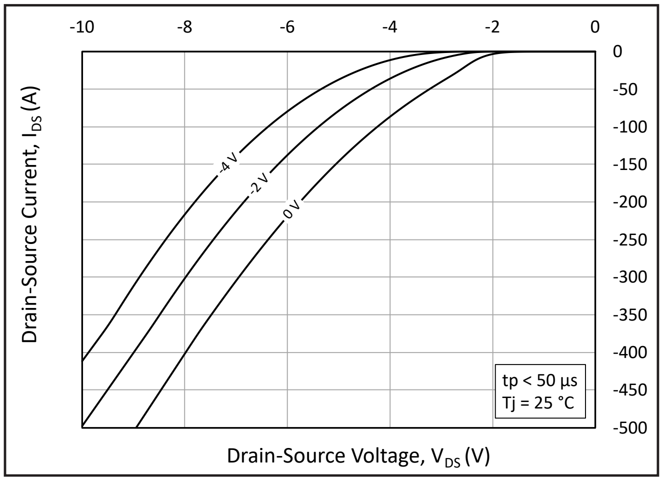


Figure 9. Body Diode Characteristic at 25°C

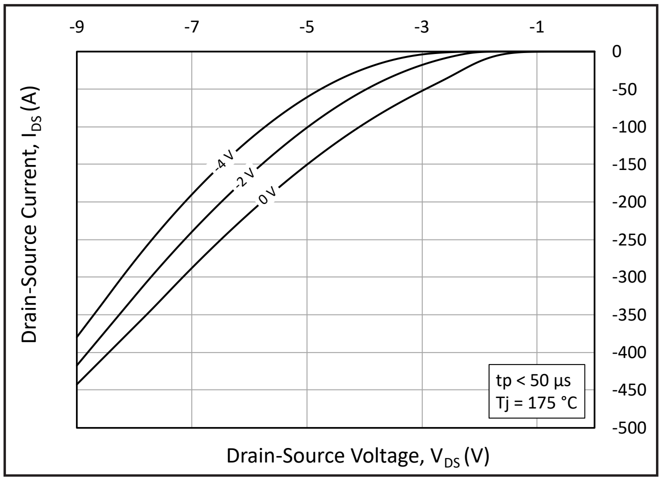


Figure 10. Body Diode Characteristic at 175°C

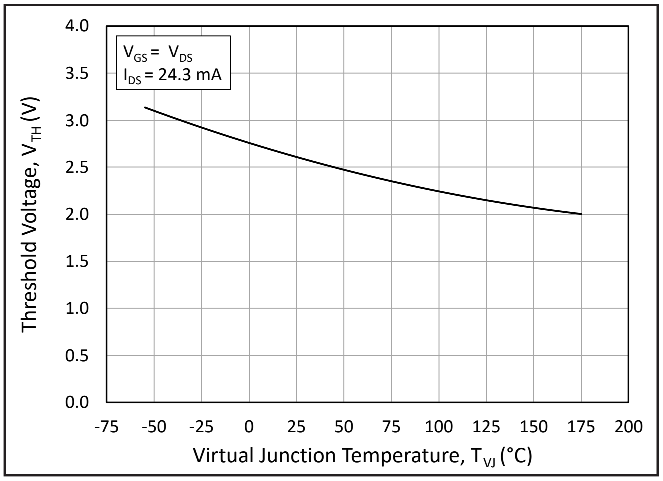


Figure 11. Threshold Voltage vs. Temperature

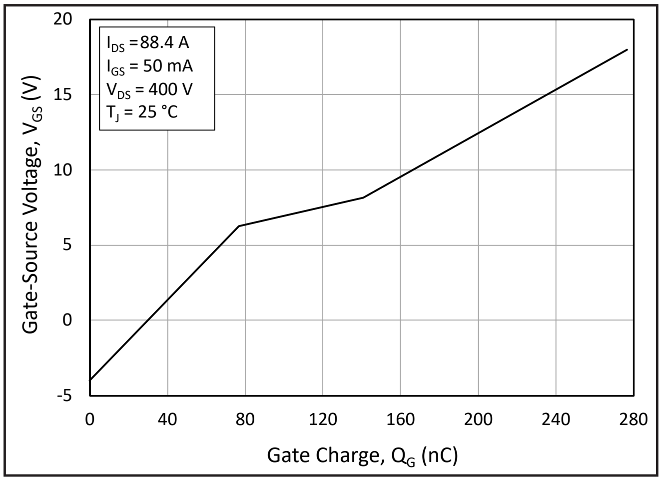


Figure 12. Gate Charge Characteristics

Typical Performance

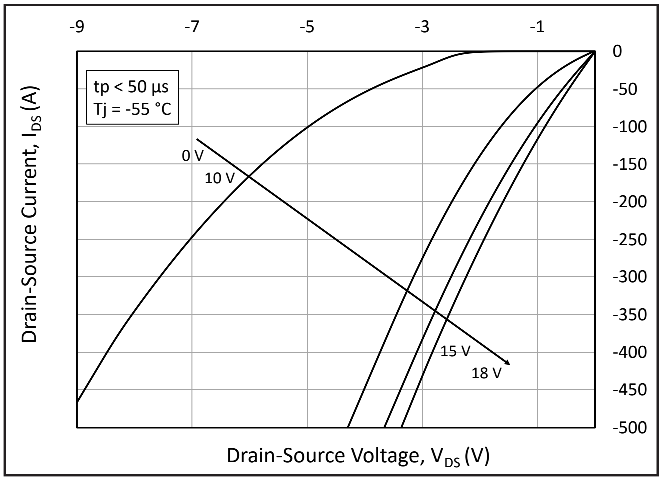


Figure 13. 3rd Quadrant Characteristic at -55°C

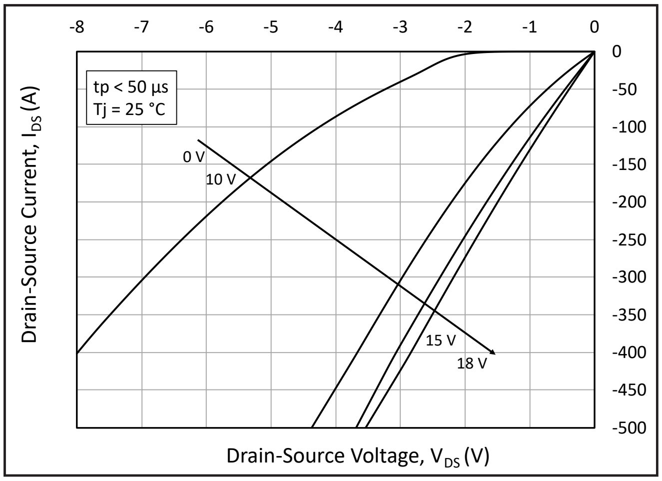


Figure 14. 3rd Quadrant Characteristic at 25°C

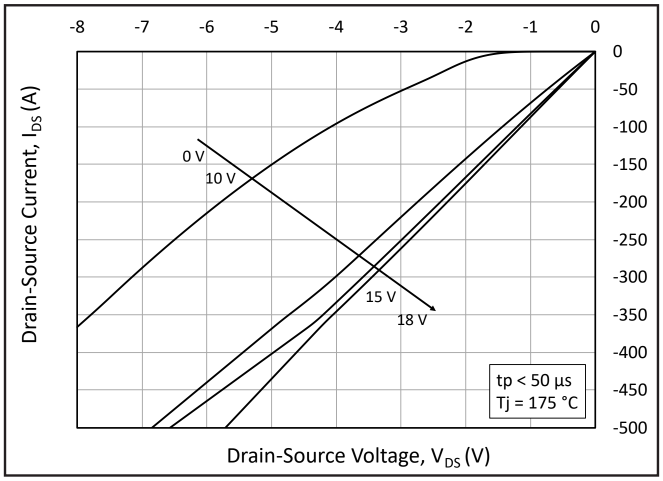


Figure 15. 3rd Quadrant Characteristic at 175°C

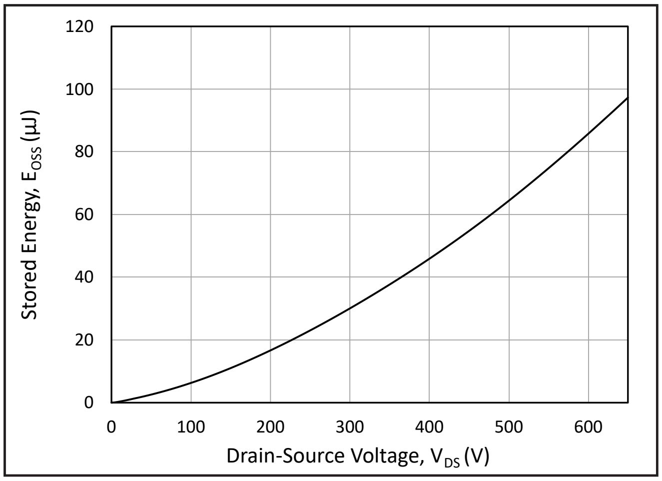


Figure 16. Output Capacitor Stored Energy

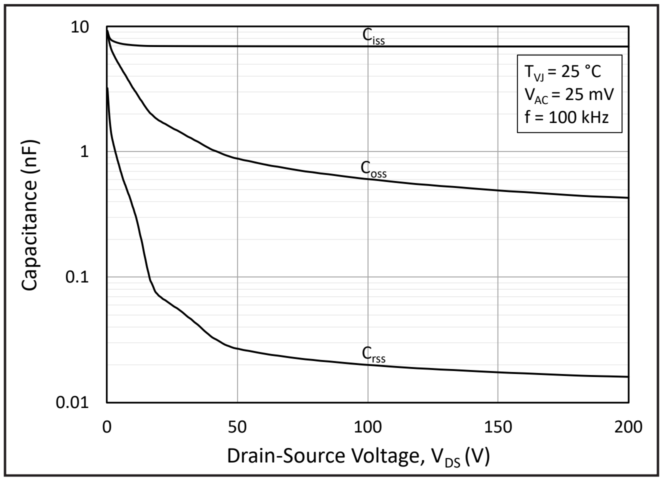


Figure 17. Capacitances vs. Drain-Source Voltage (0 - 200 V)

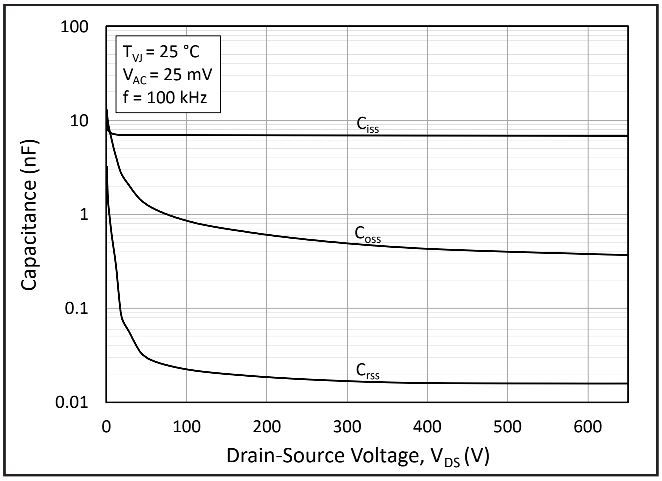


Figure 18. Capacitances vs. Drain-Source Voltage (0 - 650 V)

Typical Performance

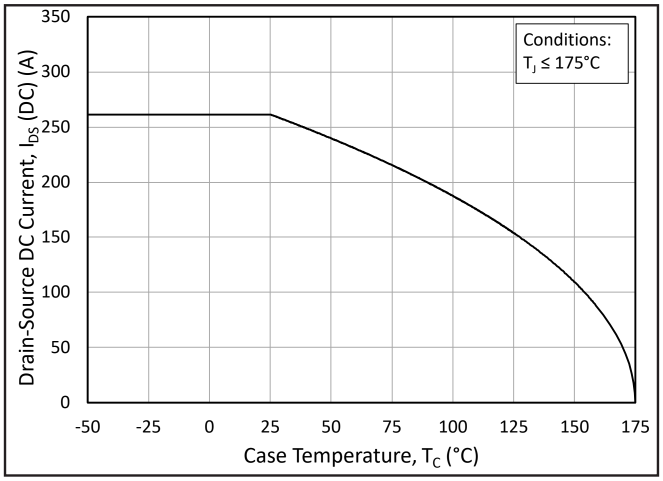


Figure 19. Continuous Drain Current Derating vs. Case Temperature

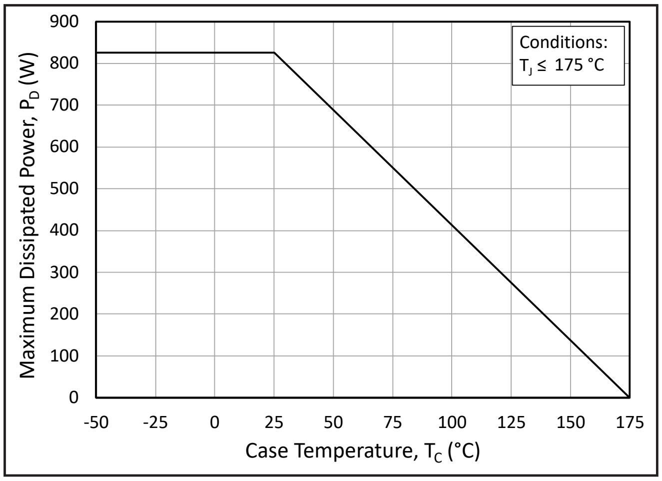


Figure 20. Maximum Power Dissipation Derating vs. Case Temperature

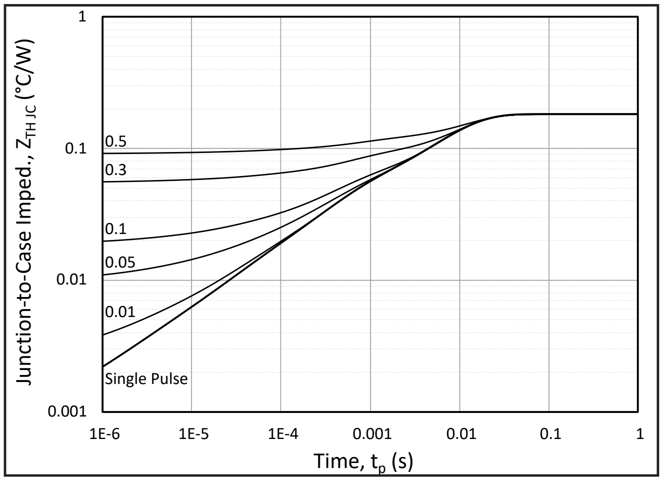


Figure 21. Transient Thermal Impedance (Junction - Case)

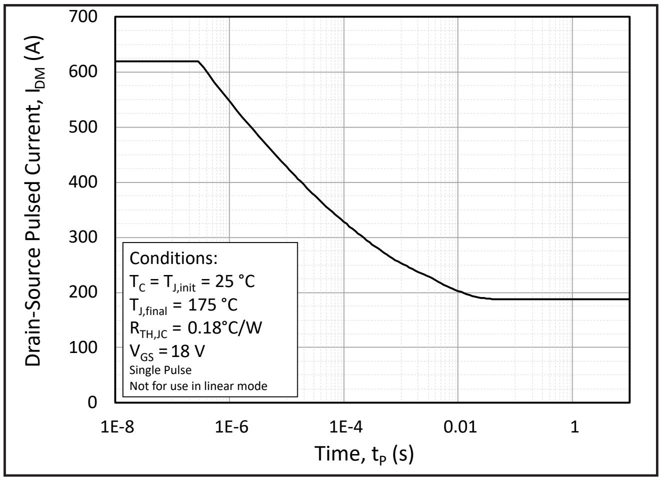


Figure 22. Pulse Current Safe Operating Area

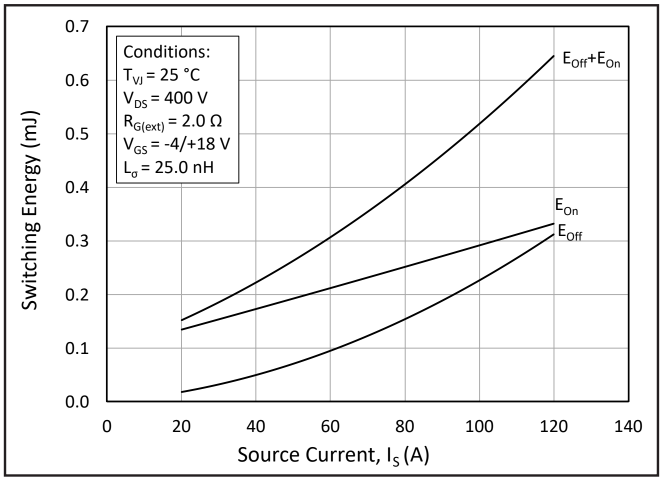


Figure 23. Clamped Inductive Switching Energy vs. Current

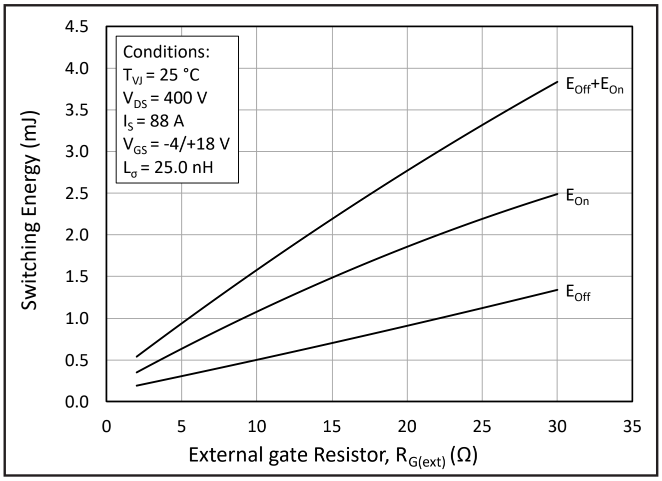


Figure 24. Clamped Inductive Switching Energy vs. $R_{G(ext)}$

Typical Performance

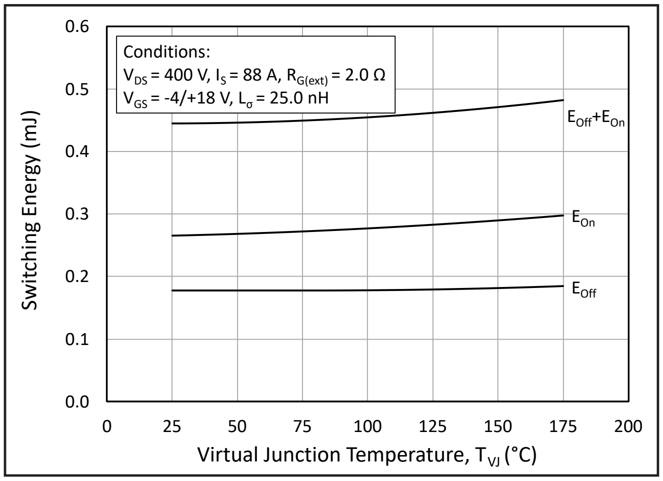


Figure 25. Clamped Inductive Switching Energy vs. Temperature

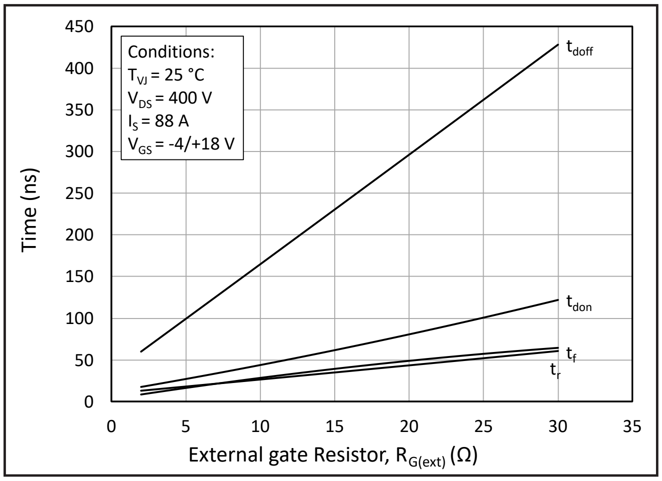


Figure 26. Switching Times vs. $R_{G(ext)}$

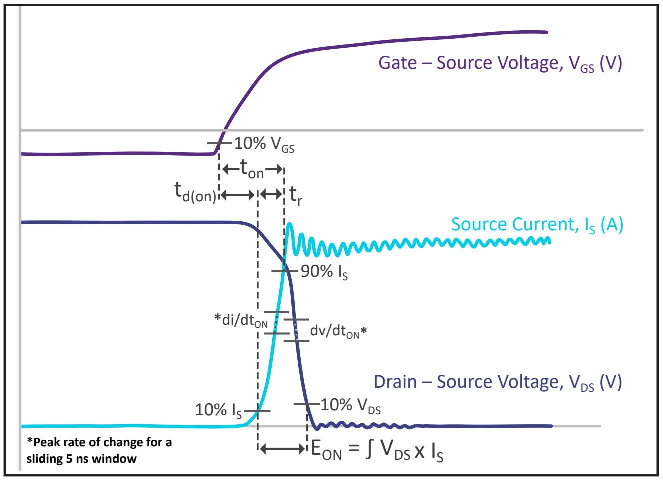


Figure 27. Turn On Switching Times Definition

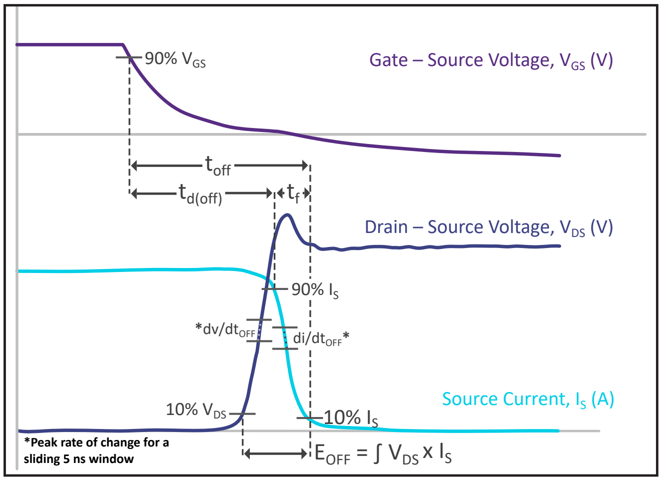


Figure 28. Turn Off Switching Times Definition

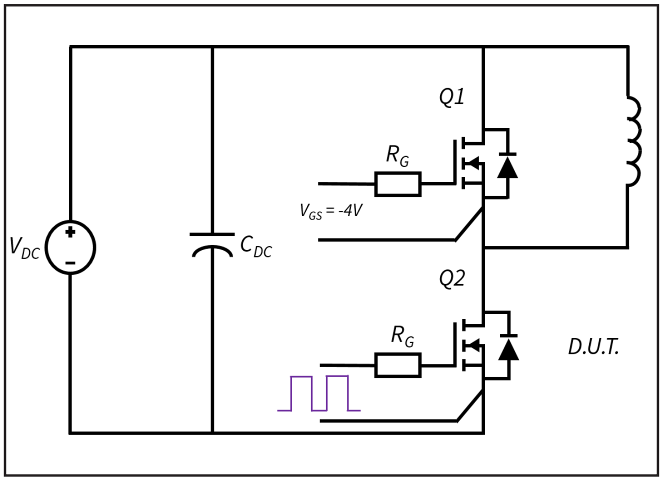


Figure 29. Clamped Inductive MOSFET Switching Waveform Test Circuit

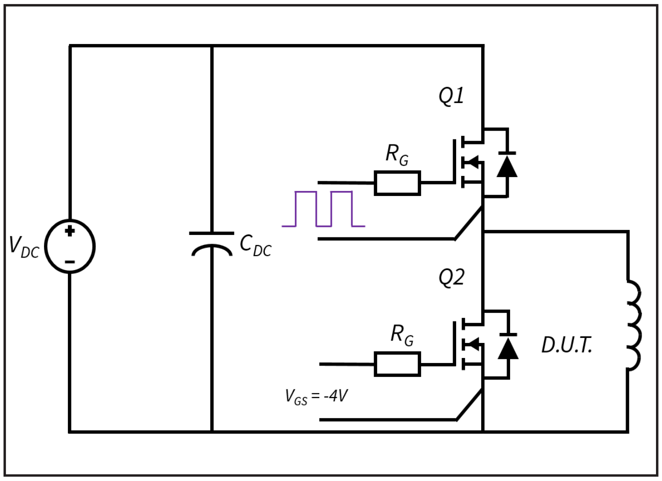
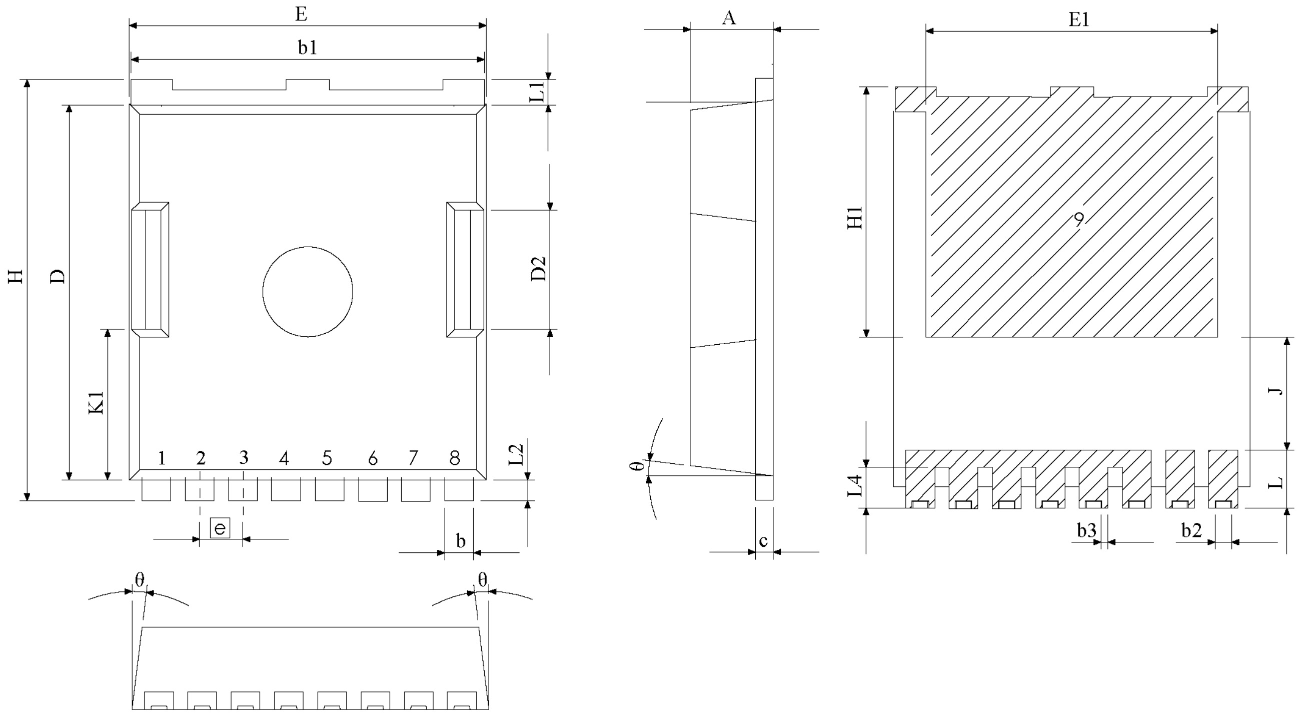


Figure 30. Clamped Inductive Body Diode Switching Waveform Test Circuit

Package Dimensions



SYMBOL	MIN (mm)	MAX (mm)
A	2.20	2.40
b	0.70	0.90
b1	9.70	9.90
b2	0.42	0.50
b3	0.07	0.27
c	0.40	0.60
D	10.28	10.58
D2	3.10	3.50
E	9.70	10.10
E1	7.90	8.30
e	1.20 BSC	
H	11.48	11.88
H1	6.75	7.15
J	3.00	3.30
K1	3.98	4.38
L	1.40	1.80
L1	0.60	0.80
L2	0.50	0.70
L4	1.00	1.30
θ	4°	10°

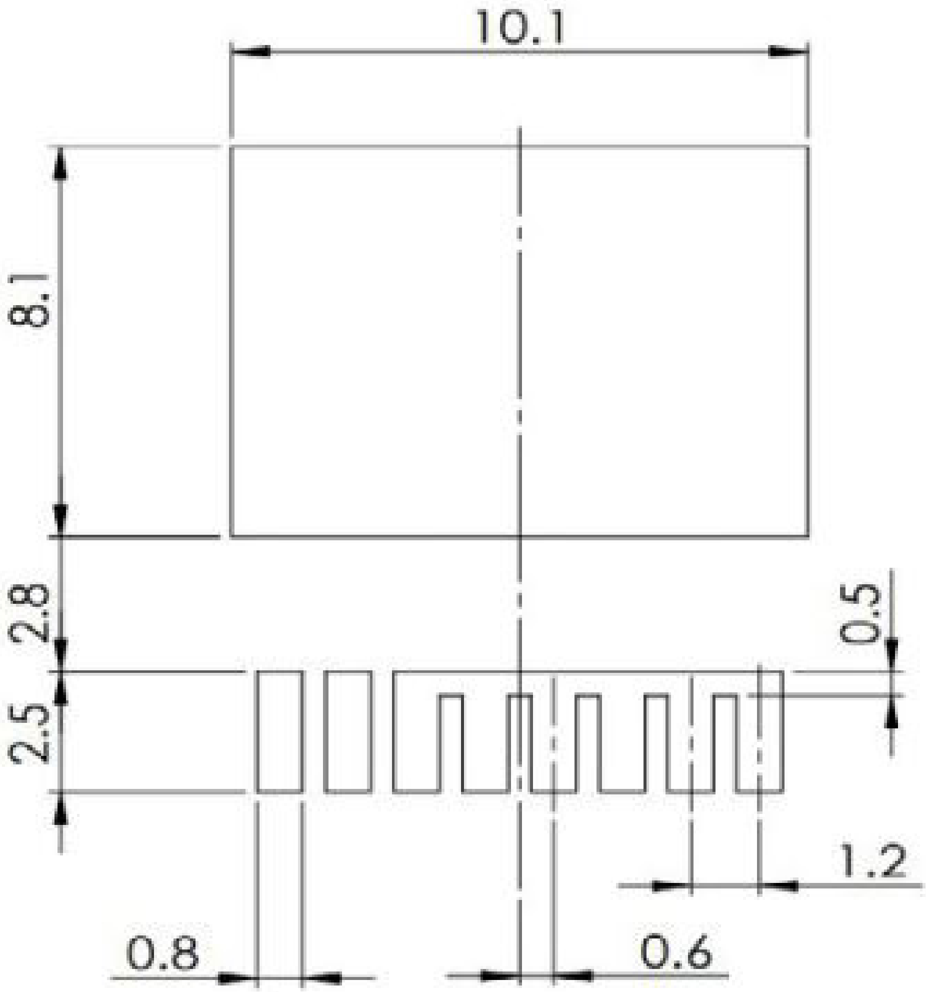
1	GATE
2	KELVIN
3-8	SOURCE
9	DRAIN

NOTE
1. ALL METAL SURFACES ARE TIN PLATED (MATTE), EXCEPT AREA OF CUT.
2. DIMENSIONING & TOLERANCING CONFORM TO ASME Y14.5M-1994.
3. ALL DIMENSIONS ARE LISTED IN MILLIMETERS. ANGLES ARE IN DEGREES.
4. PACKAGE BURR FLASH SIZE (0.5 mm) IS NOT INCLUDED IN THE DIMENSIONS

PRD-06655 Rev No. 02

Recommended Solder Pad Layout

All dimensions in mm



Revision History

Document Version	Date of Change	Description of Changes
1	June 2026	Initial Release

Appendix

Document Version	Description of Changes
A1	The following are recommendations for turning off the MOSFET with 0 V : • Measure the V_{GS} spike accurately using high -CMRR probes and low common mode noise measurements. • For the safe operation of the device, the voltage spike shall remain < 5 V for a time duration of < 40 ns.

4600 Silicon Drive | Durham, NC 27703 | Tel: +1.919.313.5300 | wolfspeed.com/power

Notes & Disclaimers

WOLFSPEED PROVIDES TECHNICAL AND RELIABILITY DATA, DESIGN RESOURCES, APPLICATION OR OTHER DESIGN ADVICE, WEB TOOLS, AND OTHER RESOURCES "AS IS" AND WITH ALL FAULTS, AND DISCLAIMS ALL WARRANTIES, EXPRESS AND IMPLIED, WITH RESPECT THERETO, INCLUDING WITHOUT LIMITATION ANY IMPLIED WARRANTIES OF MERCHANTABILITY, SUITABILITY, FITNESS FOR A PARTICULAR PURPOSE, OR NON-INFRINGEMENT OF THIRD-PARTY INTELLECTUAL PROPERTY RIGHTS.

This document and the information contained herein are subject to change without notice. Any such change shall be evidenced by the publication of an updated version of this document by Wolfspeed. No communication from any employee or agent of Wolfspeed or any third party shall effect an amendment or modification of this document. No responsibility is assumed by Wolfspeed for any infringement of patents or other rights of third parties which may result from use of the information contained herein. No license is granted by implication or otherwise under any patent or patent rights of Wolfspeed.

The information contained in this document (excluding examples, as well as figures or values that are labeled as "typical") constitutes Wolfspeed's sole published specifications for the subject product. "Typical" parameters are the average values expected by Wolfspeed in large quantities and are provided for informational purposes only. Any examples provided herein have not been produced under conditions intended to replicate any specific end use. Product performance can and does vary due to a number of factors.

This product has not been designed or tested for use in, and is not intended for use in, any application in which failure of the product would reasonably be expected to cause death, personal injury, or property damage. For purposes of (but without limiting) the foregoing, this product is not designed, intended, or authorized for use as a critical component in equipment implanted into the human body, life-support machines, cardiac defibrillators, and similar emergency medical equipment; air traffic control systems; or equipment used in the planning, construction, maintenance, or operation of nuclear facilities. Notwithstanding any application-specific information, guidance, assistance, or support that Wolfspeed may provide, the buyer of this product is solely responsible for determining the suitability of this product for the buyer's purposes, including without limitation (1) selecting the appropriate Wolfspeed products for the buyer's application, (2) designing, validating, and testing the buyer's application, and (3) ensuring the buyer's application meets applicable standards and any other legal, regulatory, and safety-related requirements.

RoHS Compliance

The levels of RoHS restricted materials in this product are below the maximum concentration values (also referred to as the threshold limits) permitted for such substances, or are used in an exempted application, in accordance with EU Directive 2011/65/EC (RoHS2), as implemented January 2, 2013. RoHS Declarations for this product can be obtained from your Wolfspeed representative or from the Product Documentation sections of www.wolfspeed.com.

REACh Compliance

REACh substances of high concern (SVHCs) information is available for this product. Since the European Chemical Agency (ECHA) has published notice of their intent to frequently revise the SVHC listing for the foreseeable future, please contact your Wolfspeed representative to ensure you get the most up-to-date REACh SVHC Declaration. REACh banned substance information (REACh Article 67) is also available upon request.

Contact info:
4600 Silicon Drive
Durham, NC 27703 USA
Tel: +1.919.313.5300
www.wolfspeed.com/power